Octal Bus Transceiver

The MC74VHCT245A is an advanced high speed CMOS octal bus transceiver fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

It is intended for two-way asynchronous communication between data buses. The direction of data transmission is determined by the level of the DIR input. The output enable pin (\overline{OE}) can be used to disable the device, so that the buses are effectively isolated.

All inputs are equipped with protection circuits against static discharge.

The VHCT inputs are compatible with TTL levels. This device can be used as a level converter for interfacing 3.3 V to 5.0 V, because it has full 5.0 V CMOS level output swings.

The VHCT245A input and output (when disabled) structures provide protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. These input and output structures help prevent device destruction caused by supply voltage—input/output voltage mismatch, battery backup, hot insertion, etc.

Features

- High Speed: $t_{PD} = 4.9 \text{ ns (Typ)}$ at $V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation: $I_{CC} = 4 \mu A$ (Max) at $T_A = 25$ °C
- TTL-Compatible Inputs: $V_{IL} = 0.8 \text{ V}$; $V_{IH} = 2.0 \text{ V}$
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Designed for 4.5 V to 5.5 V Operating Range
- Low Noise: V_{OLP} = 1.6 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance:

Human Body Model > 2000 V; Machine Model > 200 V

- Chip Complexity: 304 FETs or 76 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant

APPLICATION NOTES

- Do not force a signal on an I/O pin when it is an active output, damage may occur.
- All floating (high impedance) input or I/O pins must be fixed by means of pullup or pulldown resistors or bus terminator ICs.

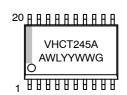


ON Semiconductor®

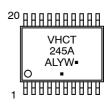
http://onsemi.com

MARKING DIAGRAMS

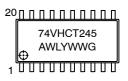












A = Assembly Location

WL, L = Wafer Lot YY, Y = Year WW, W = Work Week G or • = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

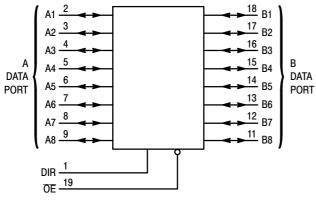


Figure 1. Logic Diagram

DIR [1 ● 20 | V_{CC} DE 2 19 A1 [A2 🛮 3 18 B1 A3 [17 B2 □ B3 A4 🛛 5 16 A5 ☐ 6 15 B4 A6 [B5 14 13 🛭 B6 A7 ∏ 8 A8 🛚 12 B7 9 GND [10 11 B8

Figure 2. Pin Assignment

FUNCTION TABLE

Contro	Inputs	
ŌE DIR		Operation
L L H	L H X	Data Tx from Bus B to Bus A Data Tx from Bus A to Bus B Buses Isolated (High–Z State)

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit	
V _{CC}	DC Supply Voltage		- 0.5 to + 7.0	V
V _{in}	DC Input Voltage	- 0.5 to + 7.0	V	
V _{I/O}	DC Output Voltage	Outputs in 3-State High or Low State	- 0.5 to + 7.0 - 0.5 to V _{CC} + 0.5	٧
I _{IK}	Input Diode Current		- 20	mA
I _{OK}	Output Diode Current (V _{OUT} < 0	GND; V _{OUT} > V _{CC})	± 20	mA
l _{out}	DC Output Current, per Pin		± 25	mA
I _{CC}	DC Supply Current, V _{CC} and GI	ND Pins	± 75	mA
P _D	Power Dissipation in Still Air,	SOIC Packages† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature		- 65 to + 150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or $V_{\rm CC}$). Unused outputs must be left open.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

†Derating - SOIC Packages: - 7 mW/°C from 65° to 125°C TSSOP Package: - 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol		Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage		4.5	5.5	V
V _{in}	DC Input Voltage		0	5.5	V
V _{I/O}	DC Output Voltage	Outputs in 3–State High or Low State	0	5.5 V _{CC}	٧
T _A	Operating Temperature		- 40	+ 85	°C
t _r , t _f	Input Rise and Fall Time	V _{CC} =5.0V ±0.5V	0	20	ns/V

DC ELECTRICAL CHARACTERISTICS

			V _{CC}	T _A = 25°C			T _A = - 40 to 85°C		
Symbol	Parameter	Test Conditions	V	Min	Тур	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		4.5 to 5.5	2.0			2.0		٧
V _{IL}	Maximum Low-Level Input Voltage		4.5 to 5.5			0.8		0.8	٧
V _{OH}	Minimum High-Level Output	I _{OH} = - 50μA	4.5	4.4	4.5		4.4		V
	Voltage $V_{in} = V_{IH}$ or V_{IL}	I _{OH} = - 8mA	4.5	3.94			3.80]
V _{OL}	Maximum Low-Level Output	I _{OL} = 50μA	4.5		0.0	0.1		0.1	V
	Voltage $V_{in} = V_{IH}$ or V_{IL}	I _{OL} = 8mA	4.5			0.36		0.44	
l _{in}	Maximum Input Leakage Current	V _{in} = 5.5 V or GND	0 to 5.5			± 0.1		± 1.0	μΑ
l _{OZ}	Maximum 3-State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or GND}$	5.5			± 0.25		± 2.5	μА
I _{CC}	Maximum Quiescent Supply Current	V _{in} = V _{CC} or GND	5.5			4.0		40.0	μА
I _{CCT}	Quiescent Supply Current	Per Input: V _{IN} = 3.4V Other Input: V _{CC} or GND	5.5			1.35		1.50	mA
I _{OPD}	Output Leakage Current	V _{OUT} = 5.5V	0			0.5		5.0	μΑ

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ns}$)

					_ _A = 25°	С	T _A = - 40) to 85°C	
Symbol	Parameter	Test Cond	itions	Min	Тур	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay A to B or B to A	$V_{CC} = 5.0 \pm 0.5 V$	C _L = 15pF C _L = 50pF		4.9 5.4	7.7 8.7	1.0 1.0	8.5 9.5	ns
t _{PZL} , t _{PZH}	Output Enable Time OE to A or B	$V_{CC} = 5.0 \pm 0.5V$ $R_L = 1k\Omega$	$C_L = 15pF$ $C_L = 50pF$		9.4 9.9	13.8 14.8	1.0 1.0	15.0 16.0	ns
t _{PLZ} , t _{PHZ}	Output Disable Time OE to A or B	$V_{CC} = 5.0 \pm 0.5V$ $R_L = 1k\Omega$	C _L = 50pF		10.1	15.4	1.0	16.5	ns
t _{OSLH} , t _{OSHL}	Output to Output Skew	V _{CC} = 5.0 ± 0.5V (Note 1)	C _L = 50pF			1.0		1.0	ns
C _{in}	Maximum Input Capacitance				4	10		10	pF
C _{out}	Maximum 3-State Output Capacitance (Output in High-Impedance State)				13				pF

		Typical @ 25°C, V _{CC} = 5.0V	
C _{PD}	Power Dissipation Capacitance (Note 2)	16	pF

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 5.0$ V)

		$T_A = 1$	25°C	
Symbol	Parameter	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	1.2	1.6	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-1.2	-1.6	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

Parameter guaranteed by design. t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|.
 C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/8 (per bit). C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74VHCT245ADWG	SOIC-20WB (Pb-Free)	38 Units / Rail
MC74VHCT245ADWRG	SOIC-20WB (Pb-Free)	1000 / Tape & Reel
MC74VHCT245ADTG	TSSOP-20*	75 Units / Rail
MC74VHCT245ADTRG	TSSOP-20*	2500 / Tape & Reel
MC74VHCT245AMELG	SOEIAJ-20 (Pb-Free)	2000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

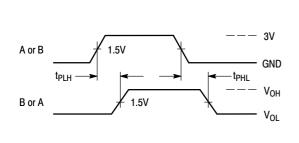


Figure 3. Switching Waveform

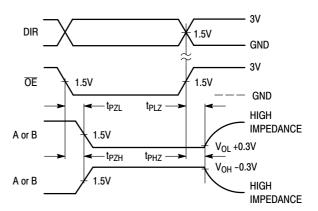
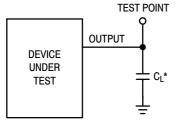
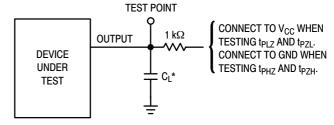


Figure 4. Switching Waveform



*Includes all probe and jig capacitance

Figure 5. Test Circuit



*Includes all probe and jig capacitance

Figure 6. Test Circuit

^{*}This package is inherently Pb-Free.

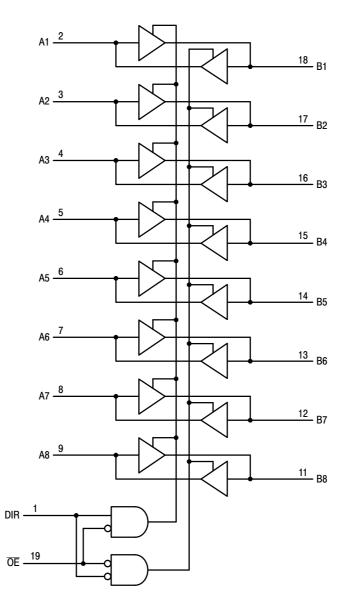
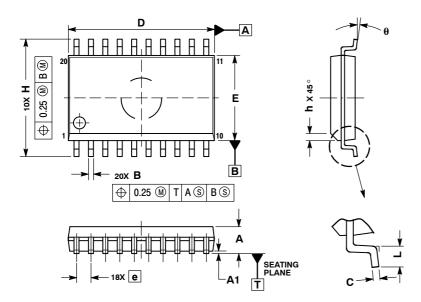


Figure 7. Expanded Logic Diagram

PACKAGE DIMENSIONS

SOIC-20 WB **DW SUFFIX** CASE 751D-05 ISSUE G

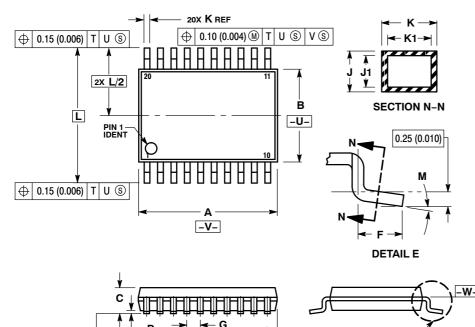


- NOTES:
 1. DIMENSIONS ARE IN MILLIMETERS.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS
DIM	MIN	MAX
Α	2.35	2.65
A1	0.10	0.25
В	0.35	0.49
С	0.23	0.32
D	12.65	12.95
E	7.40	7.60
е	1.27	BSC
Н	10.05	10.55
h	0.25	0.75
L	0.50	0.90
A	U o	7 0

PACKAGE DIMENSIONS

TSSOP-20 CASE 948E-02 **ISSUE C**



0.100 (0.004)

-T- SEATING

NOTES:

- DIMENSIONING AND TOLERANCING PER

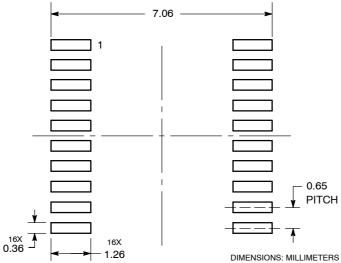
- ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION:
 MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE
 MOLD FLASH, PROTRUSIONS OR GATE
 BURRS. MOLD FLASH OR GATE BURRS. SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION
- INTERLEAD FLASH OR PROTRUSION
 SHALL NOT EXCEED 0.25 (0.10) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE
 DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.08
 (0.003) TOTAL IN EXCESS OF THE K
 DIMENSION AT MAXIMUM MATERIAL
 CONDITION.
 6. TERMINAL NUMBERS ARE SHOWN FOR
 DEFERENCE ONLY
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE —W-.

	MILLIM	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С	-	1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	0.65 BSC		BSC	
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	BSC	0.252 BSC		
M	0°	8°	0°	8°	

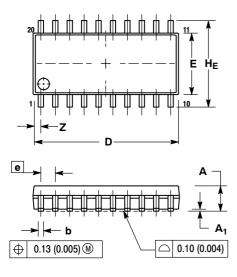
SOLDERING FOOTPRINT

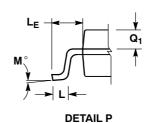
DETAIL E

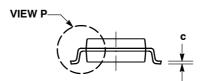


PACKAGE DIMENSIONS

SOEIAJ-20 **M SUFFIX** CASE 967-01 **ISSUE A**







NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
- B. DIMENSIONS D AND E DO NOT INCLUDE
 MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.

 THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION.
 DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.15	0.25	0.006	0.010
D	12.35	12.80	0.486	0.504
E	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050	BSC
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10°
Q_1	0.70	0.90	0.028	0.035
Z		0.81		0.032

ON Semiconductor and un are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice on semiconductor and are registered readerlands of semiconductor Components industries, Ite (SCILLC) and the series are injected to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center

Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative